

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
In re Application of Atty. Docket
MARK A. GAJDA GB010121A
Serial No.

Filed: CONCURRENTLY

TRENCH-GATE SEMICONDUCTOR DEVICES, AND THEIR MANUFACTURE
Commissioner for Patents
Alexandria, VA 22313-1450

Sir: PRELIMINARY AMENDMENT

Prior to calculation of the filing fee and examination,
please amend the above-identified application as follows:

IN THE SPECIFICATION

Before line 1, insert the following new paragraph:

--This is a Divisional of Application Serial No.

10/197,651, filed July 17, 2002.--

IN THE CLAIMS

Claims 1-6 (canceled).

7. (Original) A method of manufacturing a trench-gate semiconductor device having source and drain regions which are separated by a channel-accommodating region adjacent to the trench-gate, including the following sequence of steps:

(a) providing at a surface of a semiconductor body a masking pattern having therein a window that is used for self-aligning a gate trench and parts of the gate formed in the subsequent steps (b) to (d);

(b) etching the trench into the semiconductor body within the window, and forming a dielectric layer at the walls of the